SHANGHAI SINO-IC
MICROELECTRONICS CO., LTD.

June 2006

SEBT8550

EPITAXIAL PLANAR PNP TRANSISTOR

Features

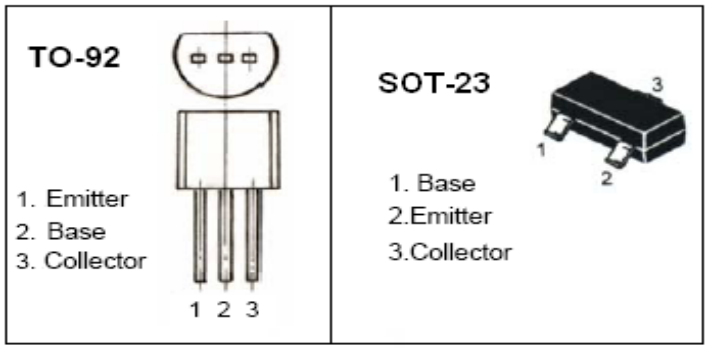
- Complementary to SEBT8550

Applications

- HIGH CURRENT APPLICATION

Construction

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Maximum Ratings (Ta=25℃)

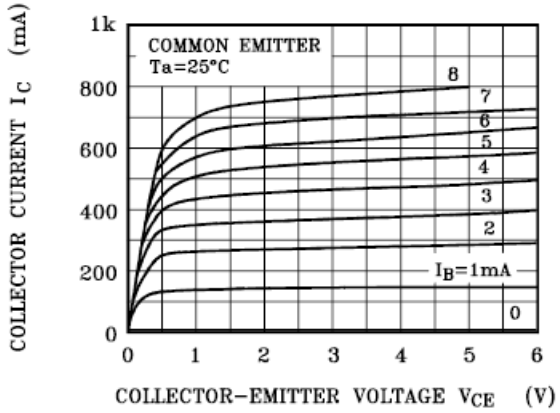
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	35	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1500	mA
Emitter Current	I_E	-800	mA
Collector Power Dissipation	P_C	625	mW
Junction temperature	T_j	150	℃
Storage temperature Range	T_{stg}	-55～ +150	℃

Electrical characteristics (Ta=25℃)

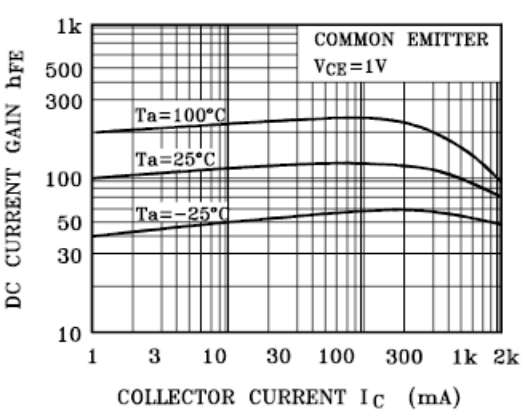
Characteristic	Symbol	Test Condition	MIN	TYP.	MAX	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=15v	-	-	50	nA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C=0.5mA	-35	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA	-30	-	-	V
DC Current Gain	h_{FE}(1) (Note)	V_{CE}=1v, I_C=50mA	100	-	300	
	h_{FE}(2)	V_{CE}=1v, I_C=350mA	60	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=500mA, I_B=20mA	-	-	0.5	V
Base-Emitter Voltage	V_{BE}	V_{CE}=1v, I_C=500mA	-	-	1.2	V
Transition Frequency	f_r	V_{CE}=5v, I_C=10mA	-	120	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, f=1MHz,	-	13	-	pF

Note: hFE(1) Classification C :100~200, D : 150~300

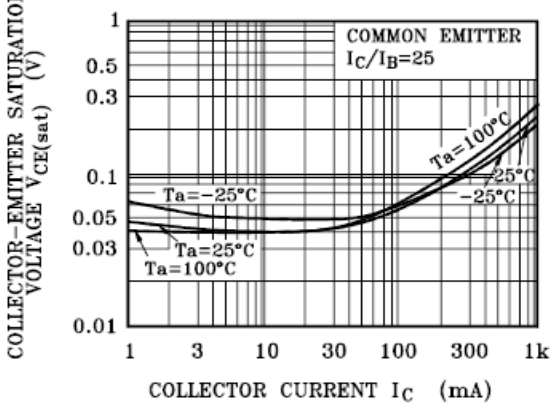
$I_C - V_{CE}$



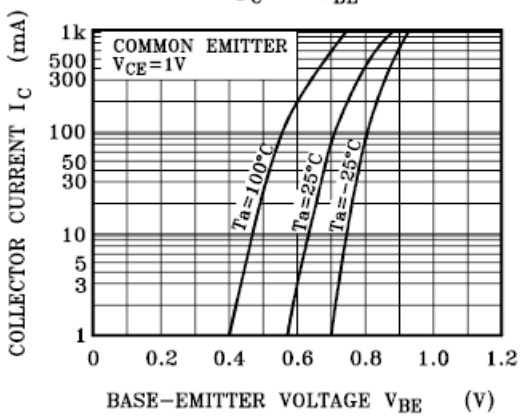
$h_{FE} - I_C$



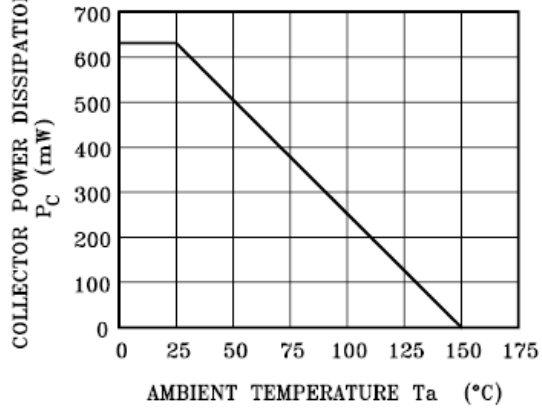
$V_{CE(sat)} - I_C$



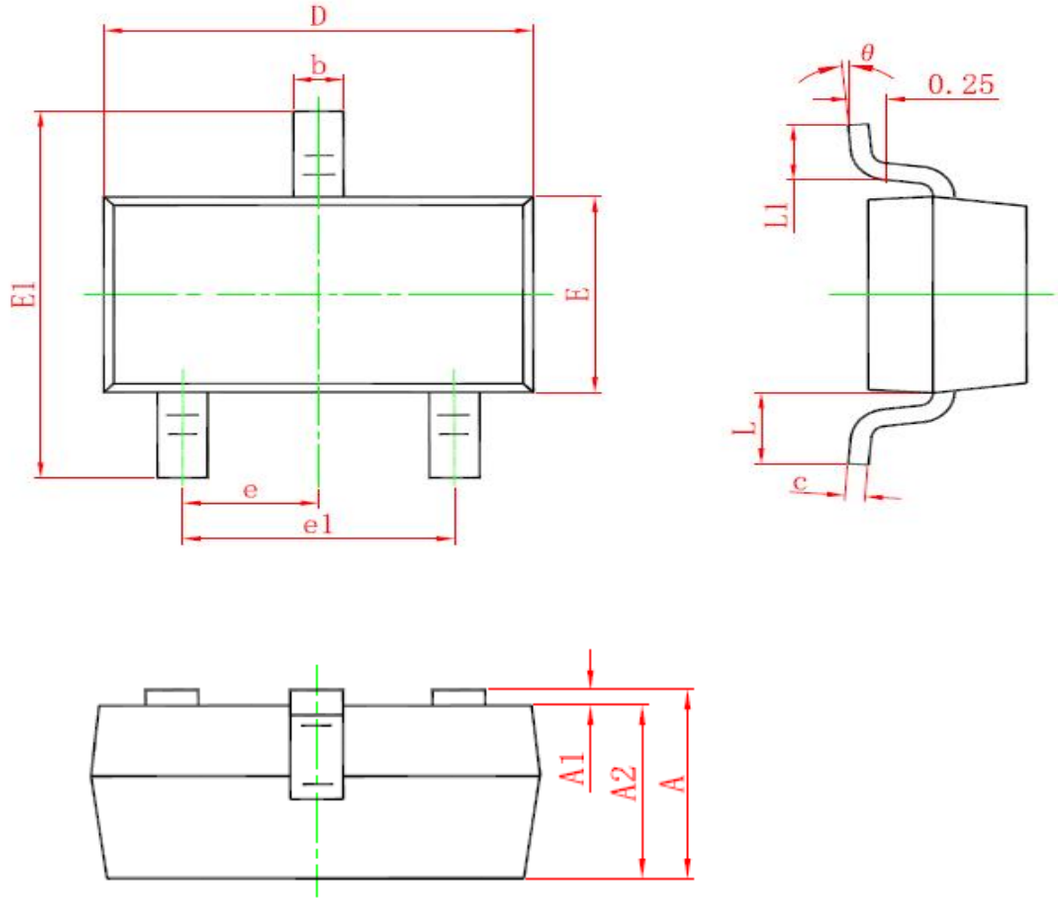
$I_C - V_{BE}$



$P_C - Ta$

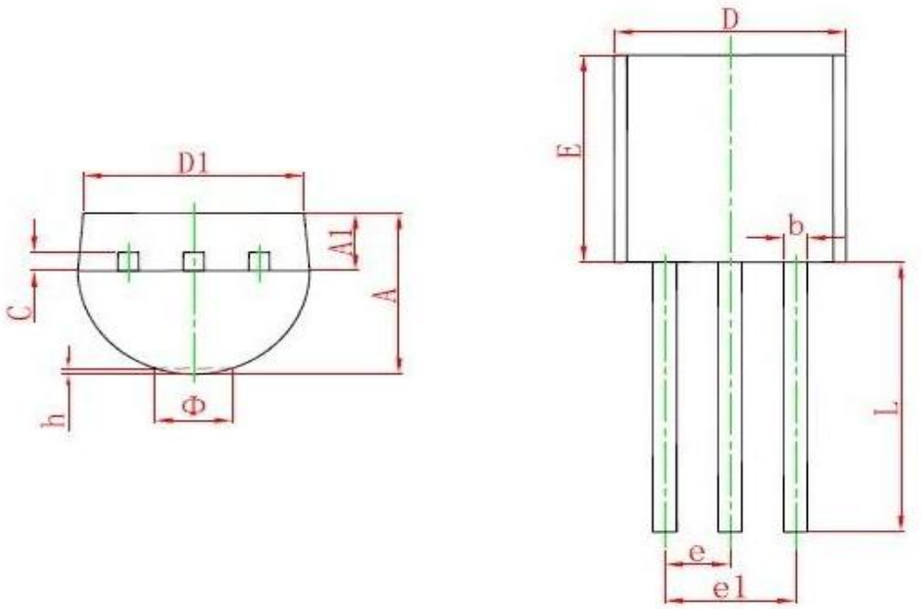


SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

TO-92 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.400	4.700	0.173	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015

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